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Supplementary information

Formation of wide-bandgap, highly transparent and compact Cd_{1-x}Zn_xS films

with dynamically controlled pH in chemical bath deposition

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Supplementary note 1:



Fig. S1 Typical representation of the dynamic maintenance of solution's pH throughout the deposition time in the chemical bath at ~10.5.

As ammonia is volatile, maintaining pH during the deposition is crucial to assess the accurate response of pH on film formation and its properties. Fig. S1 illustrates the representative curve of dynamic maintenance of the pH of the chemical bath at ~10.5. The highest and lowest pH of the solution is 10.55 and 10.44, respectively. The pH of the solution is thoroughly monitored using the pH meter, and ammonia solution is used to maintain the narrow range of the pH level. Samples are also prepared at two other pH: 9.5 ± 0.06 and 10 ± 0.06 .

Supplementary note 2:



Fig. S2 Particle size distribution with average particle size and standard deviation of all samples prepared at different pH of the bath- (a-c) 9.5, (d-f) 10 and (g-i) 10.5.

Fig. S2 depicts the particle size distribution of the prepared samples. The average particle size increases for all three Zn compositions (x= 0.2, 0.5 and 0.8). A slight variation of the average particle size (from 56 nm to 75 nm) is observed in case of fully covering, compact films (c, e and g). On the other hand, films having poor coverage (h and i) show relatively larger average particle sizes (> 100 nm).

Supplementary note 3:

Sample	pН	Zn	Cd	S
		(atom %)	(atom %)	(atom %)
$Cd_{0.8}Zn_{0.2}S$	9.5	$13.35{\pm}2.23$	$42.77{\pm}~1.02$	$43.88{\pm}1.39$
Cd _{0.5} Zn _{0.5} S		20.18 ± 1.1	$50.42{\pm}1.26$	29.40 ± 1.36
$Cd_{0.2}Zn_{0.8}S$		$20.92{\pm}1.06$	$45.61{\pm}0.98$	$33.47{\pm}0.88$
$Cd_{0.8}Zn_{0.2}S$	10	$16.37{\pm}1.44$	$52.088{\pm}1.31$	$31.55{\pm}1.29$
Cd _{0.5} Zn _{0.5} S		13.31 ± 1.48	$51.7{\pm}~1.37$	35 ± 1.53
$Cd_{0.2}Zn_{0.8}S$		$29.35{\pm}2.36$	$39.65{\pm}3.38$	$30.07{\pm}2.65$
$Cd_{0.8}Zn_{0.2}S$	10.5	$4.54{\pm}0.84$	$56.11{\pm}1.31$	$39.35{\pm}1.08$
Cd _{0.5} Zn _{0.5} S		$11.87{\pm}0.69$	45.73 ± 1.2	$42.4{\pm}~1.38$
$Cd_{0.2}Zn_{0.8}S$		$36.25{\pm}1.68$	$35.35{\pm}1.27$	$28.4{\pm}2.35$

Table S1: The obtained EDS result of the prepared samples from 10 different points.

Table S2: The obtained EDS result of the prepared optimum samples from 30 different points.

Sample	pH	Zn	Cd	S
		(atom %)	(atom %)	(atom %)
$Cd_{0.8}Zn_{0.2}S$	10.5	$4.77{\pm}0.61$	$54.54{\pm}0.82$	$40.69{\pm}0.80$
Cd _{0.5} Zn _{0.5} S	10	13.34 ± 1	$50.92{\pm}\ 1.09$	$35.73{\pm}0.96$
Cd _{0.2} Zn _{0.8} S	9.5	$19.21{\pm}0.75$	46.19 ± 0.82	34.60 ± 0.94

Supplementary note 4:

The interaction volume is found to directly proportional to the penetration depth. Penetration depth depends on the material and accelerating voltage used. It can be estimated as following [1]:

$$H = \frac{0.0276 \, A \, V^{1.67}}{Z^{0.89} \rho} \, \mu \mathrm{m}$$

Where, H= penetration depth (μ m), A= weight (g mol⁻¹), V= accelerating voltage (kV), z= atomic number and ρ = density (g cm⁻³).

Considering the film consisting solely of Cd and Zn, the penetration depth is found to be ~350 nm and ~400 nm, respectively. While calculating the penetration depth of CdS and ZnS (using the atomic number of Cd and Zn accordingly), it becomes ~600 nm and ~670 nm, respectively. Given the deposited films' thickness, the interaction between the striking electrons and the substrate is inevitable. Therefore, peaks of elements other than Cd, Zn and S are found in the EDS spectra.

Supplementary note 5:



Fig. S3 The optical bandgap (Eg) of Cd_{0.8}Zn_{0.2}S, Cd_{0.5}Zn_{0.5}S and Cd_{0.2}Zn_{0.8}S films prepared at different pH.

 E_g of all the fabricated samples except Cd_{0.2}Zn_{0.8}S film deposited at pH- 10.5 is depicted in Fig. S3. In Cd_{0.8}Zn_{0.2}S films, E_g gradually increases with the increasing pH of the bath. With increasing pH, the film formation mechanism changes from the homogeneous to the heterogeneous mechanism, resulting in improved morphology. Similar improvement of morphology increases E_g of Cd_{0.5}Zn_{0.5}S films. However, owing to the poor coverage, inconsistency in E_g is observed for Cd_{0.5}Zn_{0.5}S film deposited at pH- 10.5. Similarly, the anomaly of E_g is found in Cd_{0.2}Zn_{0.8}S film deposited at pH- 10 for incomplete coverage.



Supplementary note 6:

Fig. S4 Quadratic fit of the extracted bandgap data as a function of Zn mole fraction

The bandgap of some alloy systems follows Vegard's law and can be determined from a linear interpolation of the bandgap values as a function of constituent elements. However, the relative size of constituent elements, inhomogeneity and several other factors cause the deviation from Vegard's law. The deviation is represented by the bowing parameter determined by fitting the experimental values with a quadratic expression. The coefficient of x^2 is called the bowing parameter and is characteristic of a particular alloy system. It appears from Fig. S4 that E_g varies slowly with x for Cd-rich compositions while increasing rapidly for the Zn-rich end. A similar non-linear variation of optical band gap was also reported for solution grown Cd_{1-x}Zn_xS alloys [2].

References

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